

IN THE CLAIMS:

Please amend claims 76, 79, 80, 83, 84, 88, 91, 92, 93 and 97 as follows:

76. (Currently amended) A method of fabricating a semiconductor device comprising:
forming a semiconductor film over a substrate having an insulating surface;
irradiating the semiconductor film with a laser light to crystallize; ~~and then after~~
irradiating, annealing the irradiated semiconductor film with a light; and ~~then after~~
annealing,
patterning the semiconductor film to form at least one semiconductor island.

77. (Previously amended) A method according to claim 76 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

78. (Previously amended) A method according to claim 76 wherein said light is an infrared light.

79. (Currently amended) A method according to claim 76 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island ~~layer of the semiconductor film~~ by introducing impurities therein.

80. (Currently amended) A method of fabricating a semiconductor device comprising:
forming an insulating film on a substrate;
forming a semiconductor film on the insulating film;
irradiating the semiconductor film with a laser light to crystallize; ~~and then~~
after irradiating, annealing the irradiated semiconductor film with a light; ~~and then~~
patterning the semiconductor film to form at least one semiconductor island.

81. (Previously amended) A method according to claim 80 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

82. (Previously amended) A method according to claim 80 wherein said light is an infrared light.

83. (Currently amended) A method according to claim 80 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island ~~layer of the semiconductor film~~ by introducing impurities therein.

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84. (Currently amended) A method of fabricating a semiconductor device comprising:
forming a semiconductor film over a substrate having an insulating surface;
~~introducing~~ applying a material comprising metal for promoting crystallization to the semiconductor film;
irradiating the semiconductor film with a laser light to crystallize; ~~then~~
after irradiating, annealing the irradiated semiconductor film with a light; and ~~then~~
after annealing, patterning the semiconductor film to form at least one semiconductor island.

85. (Previously amended) A method according to claim 84 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

86. (Previously amended) A method according to claim 84 wherein said light is an infrared light.

87. (Previously amended) A method according to claim 84 wherein said metal is at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag and Au.

88. (Currently amended) A method of fabricating a semiconductor device comprising:
forming a semiconductor film over a substrate having an insulating surface;
crystallizing the semiconductor film by a laser irradiation with a laser light; ~~then~~
after the laser irradiation, annealing the irradiated semiconductor film with a light so as to improve crystallinity of the semiconductor film;

heating the annealed semiconductor film in an atmosphere comprising nitrogen; and ~~then~~
after heating, patterning the semiconductor film to form at least one semiconductor island.

89. (Previously amended) A method according to claim 88 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

90. (Previously amended) A method according to claim 88 wherein said light is an infrared light.

91. (Currently amended) A method according to claim 84 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island ~~layer of the semiconductor film~~ by introducing impurities therein.

92. (Currently amended) A method according to claim 88 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island ~~layer of the semiconductor film~~ by introducing impurities therein.

93. (Currently amended) A method of fabricating a semiconductor device comprising:
forming a semiconductor film over a substrate having an insulating surface;
introducing a material comprising metal for promoting crystallization to the semiconductor film;

irradiating the semiconductor film with a laser light to crystallize; ~~then~~
after irradiating, annealing the irradiated semiconductor film with a light;
after annealing, patterning the semiconductor film to form at least one semiconductor island; and
forming a gate insulating film over the semiconductor island.

94. (Original) A method according to claim 93 wherein said laser light is selected from the group consisting of KrF, XeCl, XeF, and ArF.

95. (Original) A method according to claim 93 wherein said light is an infrared light.

96. (Original) A method according to claim 93 wherein said metal is at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag and Au.

97. (Original) A method according to claim 93 further comprising a step of heating the annealed semiconductor film in an atmosphere comprising nitrogen.

97. (Currently amended) A method according to claim 93 further comprising a step of forming at least channel, source, and drain regions in the semiconductor island ~~layer of the semiconductor film~~ by introducing impurities therein.

98. (Original) A method according to claim 76, wherein said semiconductor device comprises a CPU on the substrate.

99. (Original) A method according to claim 80, wherein said semiconductor device comprises a CPU on the substrate.

100. (Original) A method according to claim 84, wherein said semiconductor device is used in a CPU on the substrate.

101. (Original) A method according to claim 88, wherein said semiconductor device comprises a CPU on the substrate.

102. (Original) A method according to claim 93, wherein said semiconductor device comprises a CPU on the substrate.